



# JX Nippon Mining & Metals Corporation Company Introduction

October, 2018



# JXTG Holdings

Aiming to develop into one of the most prominent and comprehensive energy, resources and materials company groups in Asia

Listed subsidiaries  
NIPPO/Toho Titanium

## JX Nippon Oil & Gas Exploration

Crude oil and natural gas production  
(a project company basis)

**128** thousand  
barrels/day

Crude oil equivalent (FY2016 actual)

## JXTG Nippon Oil & Energy

A leap forward to become a standout market leader



Market Share of  
domestic sales of petroleum products

**50%**

FY2016 actual: No. 1 in Japan

Established presence in the global market



Paraxylene

※1

No. 1 in world **3.62** million  
tons/year

Propylene

No. 1 in Asia **1.7** million  
tons/year

## JX Nippon Mining & Metals

Equity entitled copper mine production

**200** thousand  
tons/year

contained in copper concentrate (FY2016 actual)

Refined copper production capacity

**920** thousand  
tons/year

on equity stake basis as of March 2017 ※2

Electronic Materials

Products with world No.1 market shares

# JX Nippon Mining & Metals Corporation (JX-NMM)

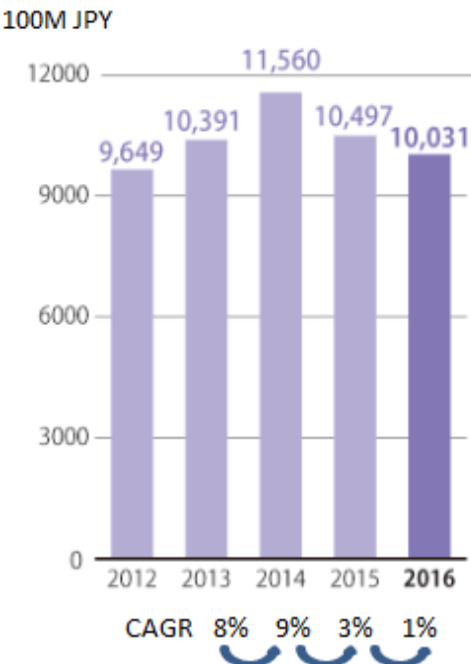


Company Name	JX Nippon Mining & Metals Corporation
Head Office	Otemachi, Chiyoda-ku, Tokyo, Japan (in front of Imperial Palace)
Establishment	Y1905 as mining company in Hitachi
Capital	¥20,000 Million
Stock Holder	100% JXTG Holdings, Inc.
Employees	2,600 employees (as of 2017.1. 1)

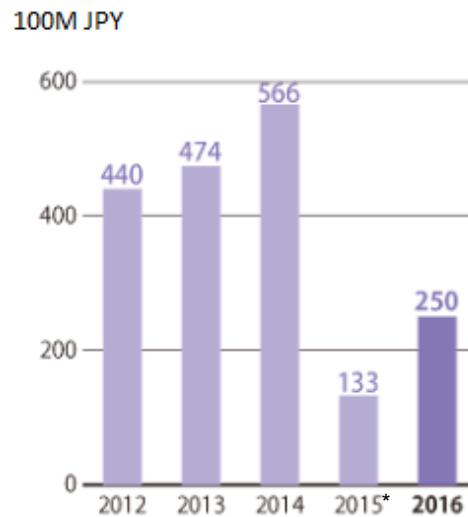


# JX- NMM Consolidated Financial Result

## Sales Revenue

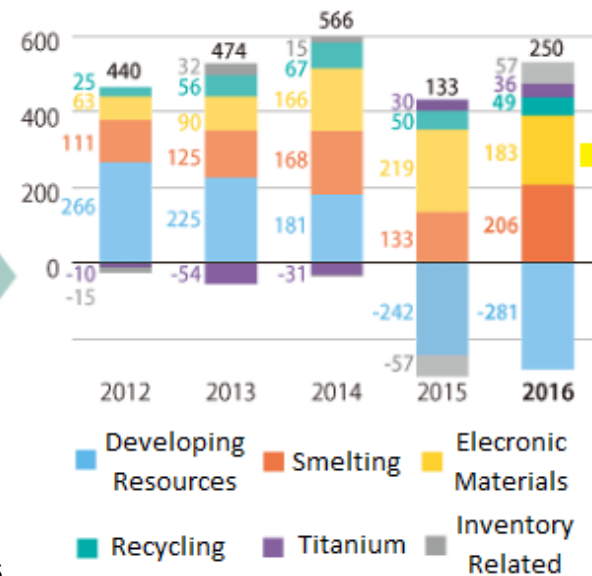


## Income



\* Impairment for "Developing Resources" : ≒ M\$ 825

## <Segments>

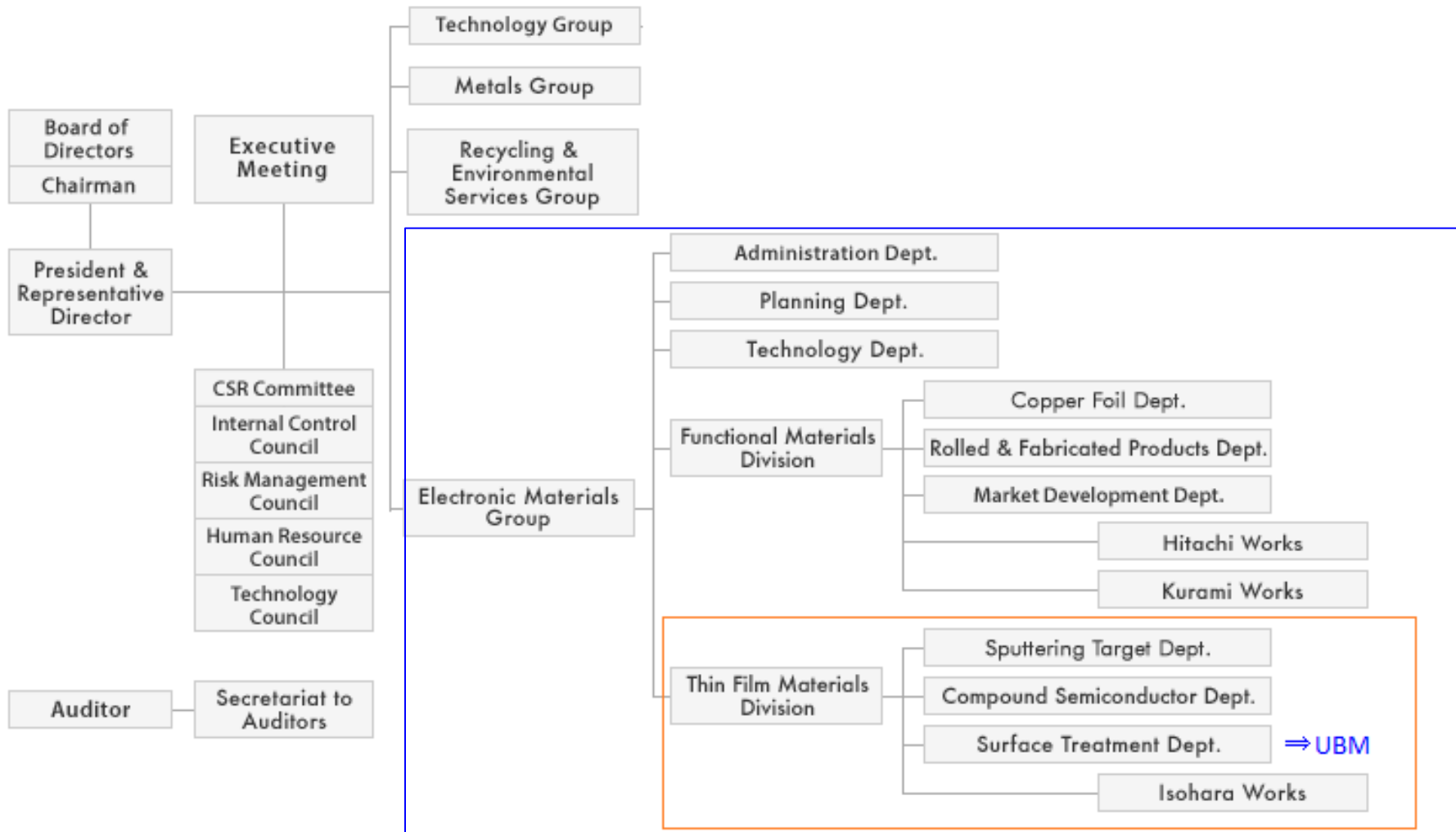


Electronic Materials  
2017 Financial FCST

250\*

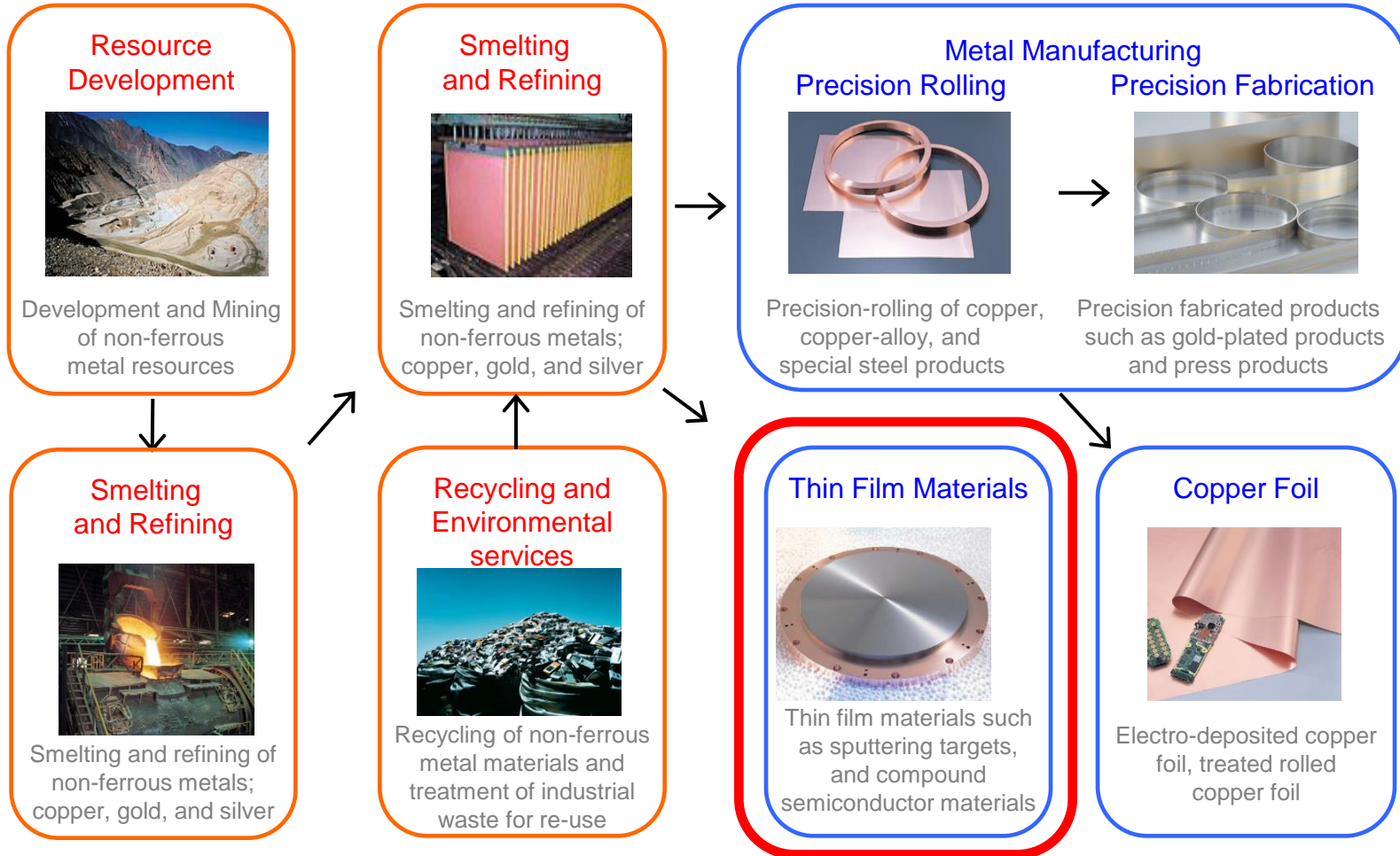
\* JX-NMM will adopt IFRS since 2017.

# Organization Chart of JX-NMM



## Metals

## Electronic Materials

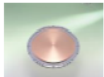
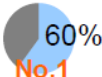

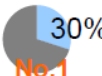

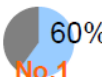
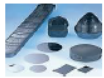
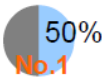

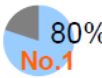

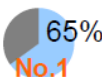

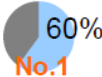

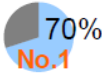


# JX Metal Business Electronic Materials Share



## Metals Business

### Electronic Materials

Main products	Global market share	Primary applications	End-use applications				
			PCs	Mobile phones / Smart phones	Digital, Avs	Telecom infra/ Data center	Auto mobiles
 Semiconductor targets		CPUs, memory chips, etc.	◎	◎	◎	◎	○
 ITO targets for FPDs *		Transparent electrodes	◎	◎	◎		○
 HD media targets		HDD (Hard disk drives), etc.	◎			◎	
 In-P compound semiconductors		Optical communication devices, High-speed IC			○	◎	○
 Treated rolled copper foil		Flexible printed circuit boards	○	◎	◎		○
 Phosphor bronze		Connectors, Springs for electronic materials	○	◎	○		○
 Corson alloy (C7025)		Connectors, Lead frames	○	◎	○	○	○
 Titanium copper alloy		High-class connectors, etc.	○	◎	○		○

\* Flat Panel Displays

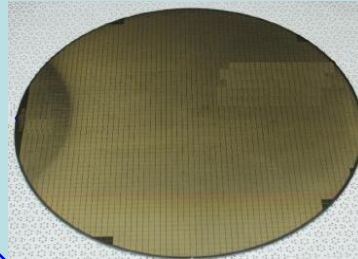
# Products of Surface Treatment Department



※Product written in blue letters is under developing

Products :  
Materials for  
Semiconductor  
wiring &  
interconnection  
/Subcontracting  
service for E-less  
UBM plating layer

E-less UBM plating



Applied for Semiconductor  
packaging

Low- $\alpha$  Sn



Low- $\alpha$  Sn materials for  
solder, plating solution and  
so on

CuP anode



Anode materials for Cu  
plating of wafers

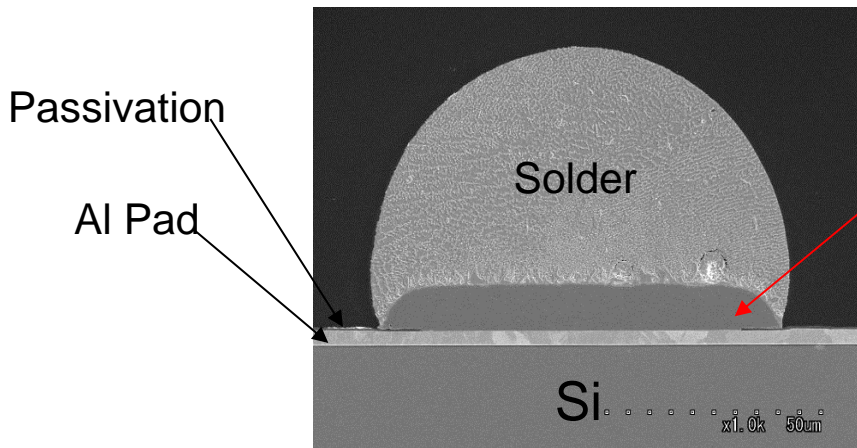
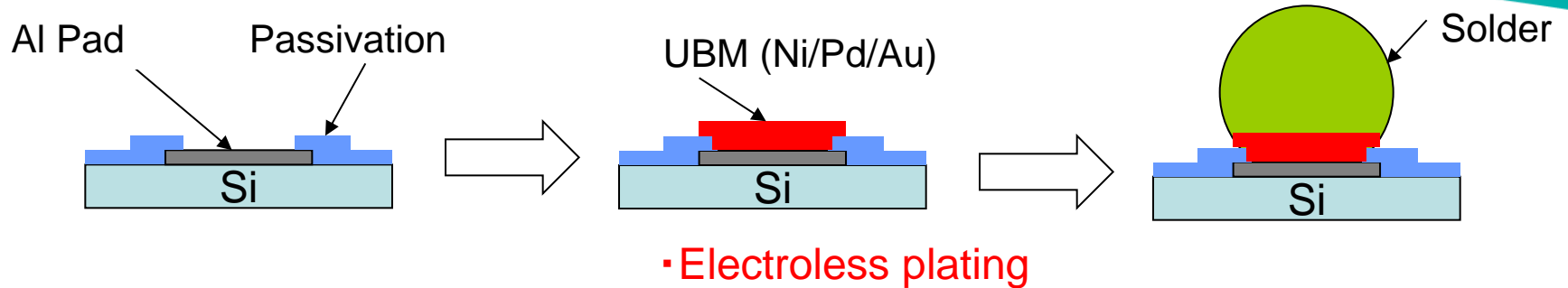


Cu paste



# What is UBM-Solder Bumping?

Under  
Bump  
Metallization



## UBM (Ni/Pd/Au)

- Ni: Barrier layer of solder diffusion
- Pd: Barrier layer of Ni diffusion
- Au: Widen process window for bonding  
Solder Wettability

Fig. Cross section of Bumping on Pad

# Advantages of E-less UBM



## Comparison between Electroless and Electrolytic plating

### Advantages

✓ **Low Cost:** High selectivity (Plating on the selected portion)  
Selective plating with short process  
--- No Mask (high flexibility for changing chip design)  
No Metal Sputtering needed

✓ **High Throughput:** Batch Processing of Multiple Wafers  
No wafer size requirement, No photo-process

✓ **Fine pattern:** No electrode needed

### Drawbacks

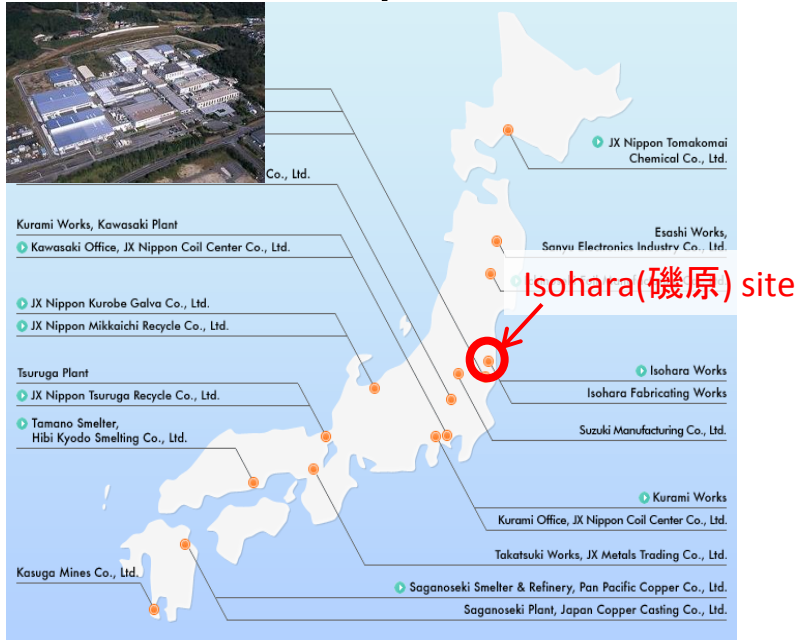
✓ **High sensitivity:** Susceptible to electrical potential difference between pads,  
surface contaminations and Si exposed portion (scribe line)

✓ **Resist/Passivation attack:** Resist and passivation are attacked  
by plating solution in some cases.

# UBM Production Site



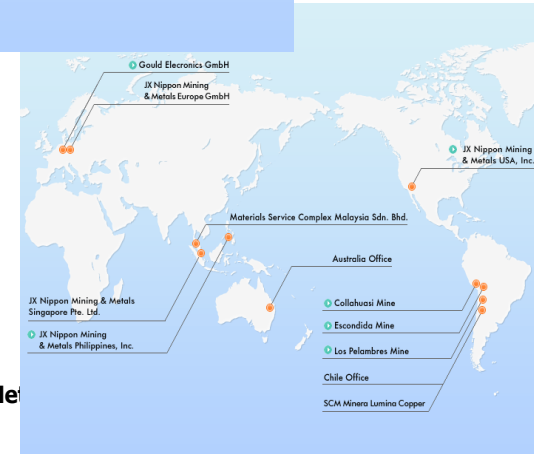
## Japan



## Taiwan



2 production sites related to UBM



# Japan Isohara(磯原) site

--- Mass production, Trial production, Sample analysis



Full-Automatic Plating Line #1



Full-Automatic Plating Line #2

2007.6 Production Line#1 and #2 installed

2008.1 Operation started

2010.12 Production Line#3 installed

2011.5 Operation started

**JX Nippon Mining & Metals Corporation**

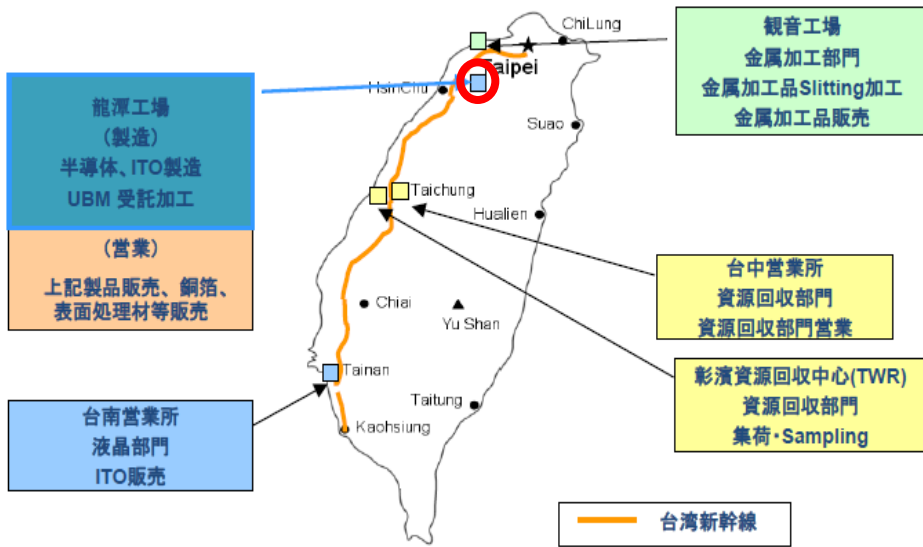


Full-Automatic Plating Line #3

# Taiwan Longtan(龍潭) site --- Mass production



Dec. 2014 Installed  
Feb. 2015 Operation started

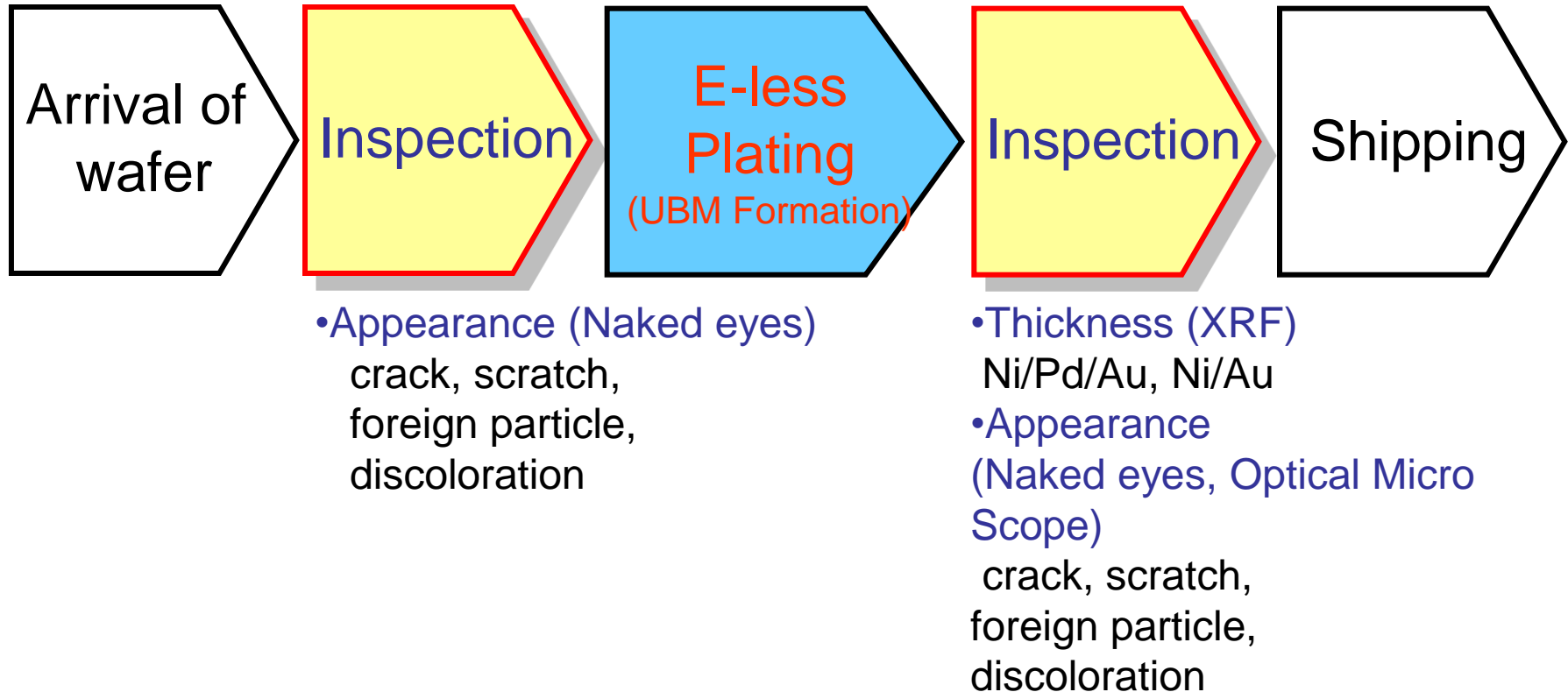


# Capacity

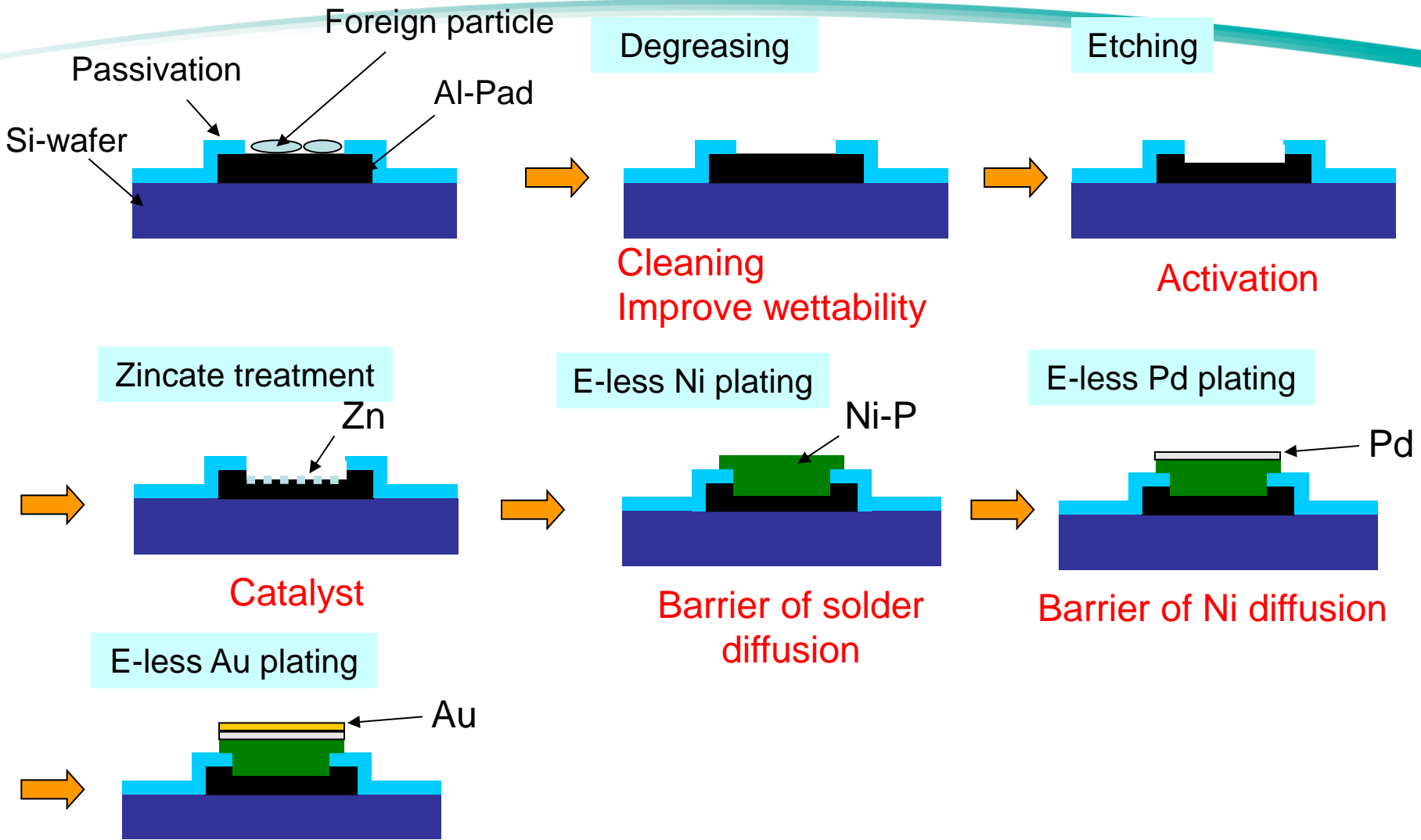


Location	Taiwan	Japan
Plating Line	1 line	3 line (2 of 3line are occupied)
Equipment capacity (pcs/month)	30,000	39,000
Current capacity (pcs/month)	20,000	15,000

# JX's Electroless-plating UBM service



# Basic process of E-less plating for UBM -- Ni/Pd/Au process



Widen process window for bonding  
Wettability for solder



# Features of JX's E-less Ni/(Pd)/Au UBM



Table Typical features of the process

<b>Ni (material)</b>	<b>Ni- P (P: 5~10wt%)</b>
<b>Ni thickness</b>	<b>1.5~5.0<math>\mu</math>m should consider pad spacing</b>
<b>Pd thickness (center value)</b>	<b>0.05~0.2<math>\mu</math>m</b>
<b>Au thickness (center value)</b>	<b>0.02~0.2<math>\mu</math>m (Ni/Pd/Au: max.0.05um, Ni/Au: max.0.2um)</b>
<b>Thickness uniformity</b>	<b>Less than <math>\pm 10\%</math> in 200mm wafer</b>
<b>Shear strength</b>	<b>100MPa (typical data)</b>
<b>Al etching</b>	<b>0.1<math>\mu</math>m (for AlCu, AlSiCu) 0.5<math>\mu</math>m (for AlSi)</b>

# JX's Electroless plating for UBM



Property	Specification (Mass production in Longtan)	Specification (Trial production in JPN site)
Wafer	Si	Si, GaAs, SiC, GaN
Bond pad metal	Al, AlSi, AlSiCu, AlCu	AlCu, AlSiCu, AlSi, Al, Au, Cu
Bond pad thickness	$\geq 1\mu\text{m}$	min. $0.4\mu\text{m}$
Passivation	SiN, SiO <sub>2</sub> , polyimide	← See left
Residues on bondpads (inorganic, organic)	Not acceptable	← See left
Wafer size	$\leq 300\text{mm}$ (12")	← See left
Wafer thickness	$\geq 200\mu\text{m}$	$80\mu\text{m}$ (6") , $130\mu\text{m}$ (8")
Bond pad geometry	Square, rectangular, round, octagonal and any others	← See left
Passivation opening	$\geq 60\mu\text{m}$	min. $4\mu\text{m}$
Bond pad spacing	$\geq 20\mu\text{m}$ (depends on Ni thickness)	min. $7\mu\text{m}$ (depends on Ni thickness)
Wafer fabrication process	CMOS, power device, MEMS and any others	← See left
Ink dots	Not acceptable	← See left
Probe marks	Acceptable	← See left
Scribe lines	SiO <sub>2</sub> , SiN (must be passivated)	← See left

## Inspection equipment (Taiwan & Japan)

### Measurement of plated film thickness

Fluorescent X-ray(XRF)  
Analyzer



### Wafer micro visual inspection

Wafer Microscope



# Characteristic evaluation equipment(Japan site only)



Reflow Oven



Wire bonder



## Bondtester

Evaluation for reliability of  
Solder joint & Wire bonding



## Solder checker

Evaluation for Solderability  
(Solder wettability)

## Instruments for Surface morphology



Noncontact 3D Measuring  
Equipment  
(Surface profile)



FE-SEM  
(High mag. Observation)



FIB-SIM  
(X-section)



SPM  
(Surface profile)

STEM (in Hitachi)

# Analytical equipment(Japan site only)



## Instruments for Functional group analysis



FT-Raman

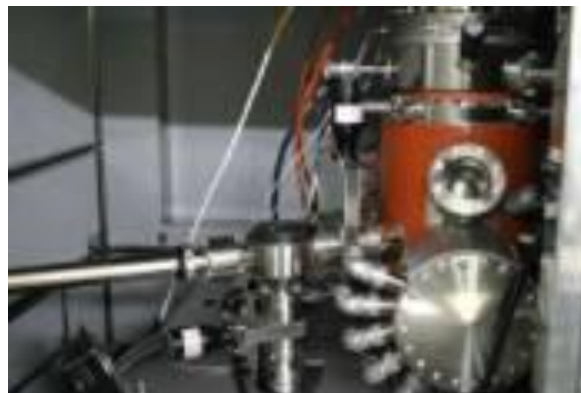


FT-IR

## Instruments for Elemental analysis



FE-EPMA



FE-AES

XPS  
(in Hitachi)

## Relationship between the JX Nippon Mining & Metals Group and Society

Nonferrous metals play an indispensable role as materials in contemporary life, and of all such metals, copper is particularly notable for its good electrical conductivity and ease of processing. Copper is therefore used in a whole variety of applications, from electrical wires, buildings, and consumer electronics such as air conditioners and refrigerators, to state-of-the-art electronic devices such as LCD televisions, PCs, and smartphones, and even in cars and trains.

The titanium manufactured by the Toho Titanium Group is likewise used in a wide variety of day-to-day applications, being light, strong, and resistant to corrosion.

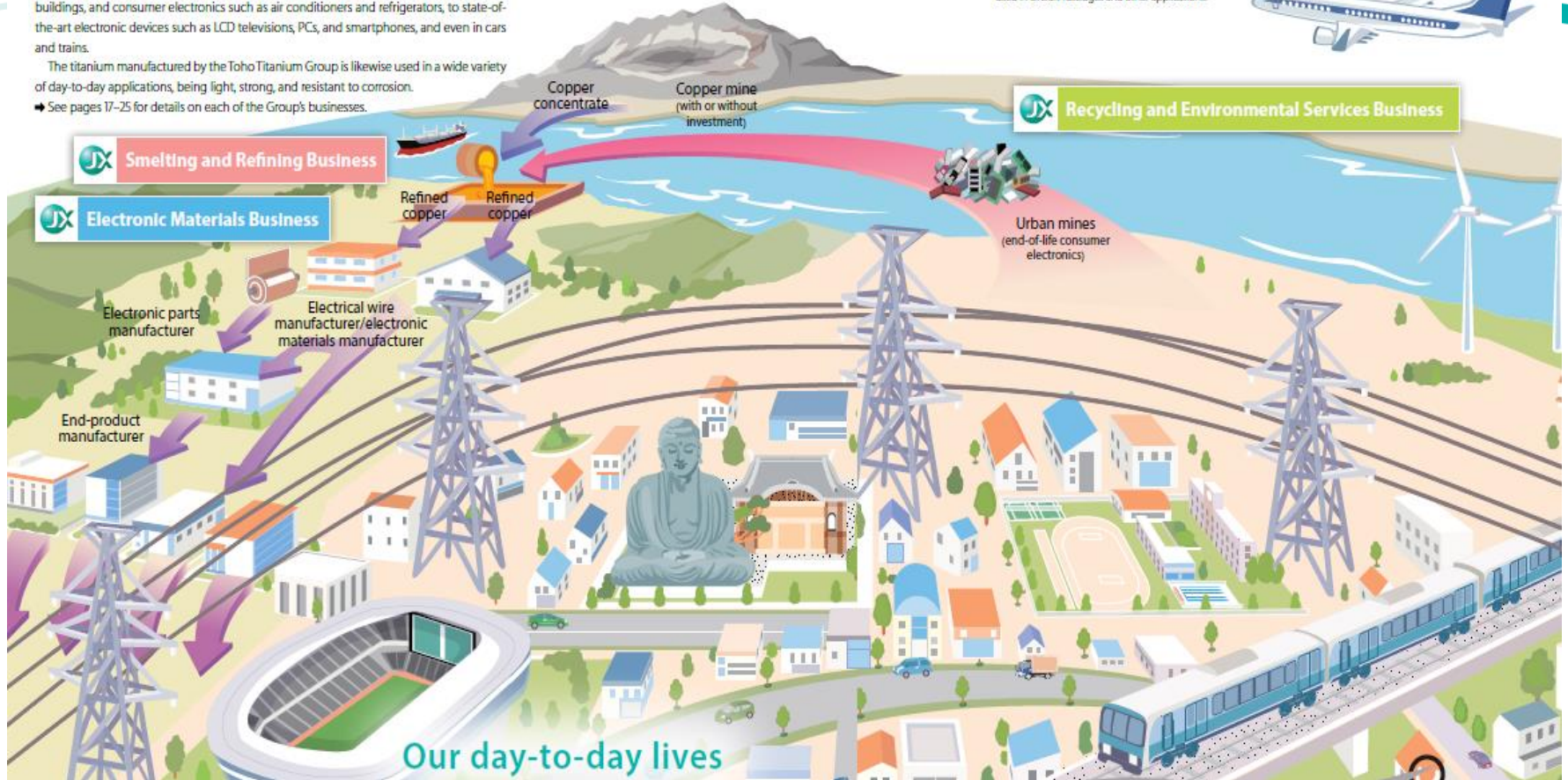
➔ See pages 17-25 for details on each of the Group's businesses.

**JX Resources Development Business**

**JX Titanium Business**

\* Light, strong, and corrosion-resistant titanium is used in aircraft fuselages and other applications.

**JX Recycling and Environmental Services Business**



# Thank you for listening!





# Appendix

## Example of Defect Mode

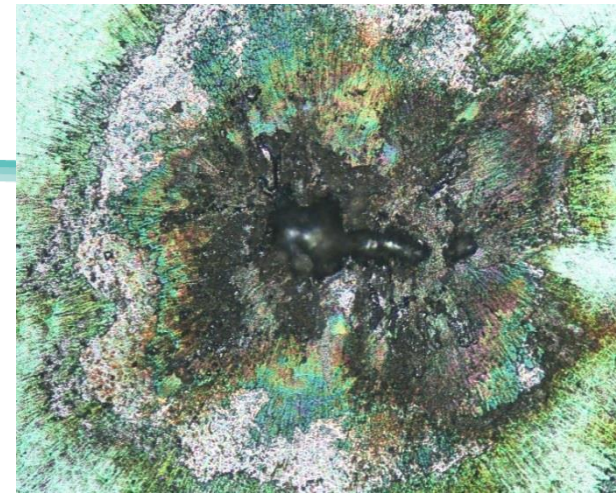
# Example of unsuitable wafer for Electroless plating (1)

exposed portion (Abnormal plating)

Si



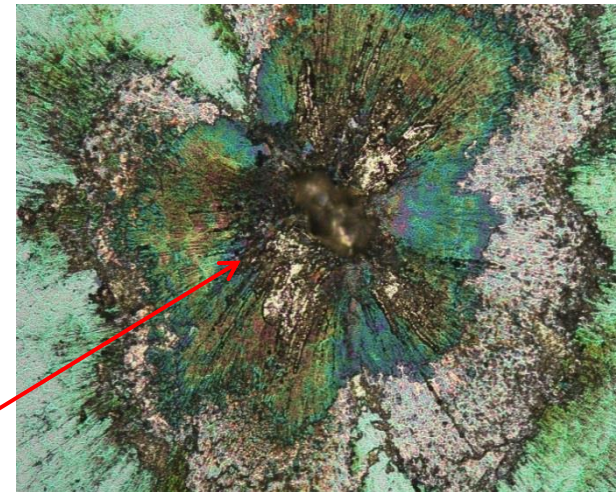
Au deposition



X

× 200

Plating

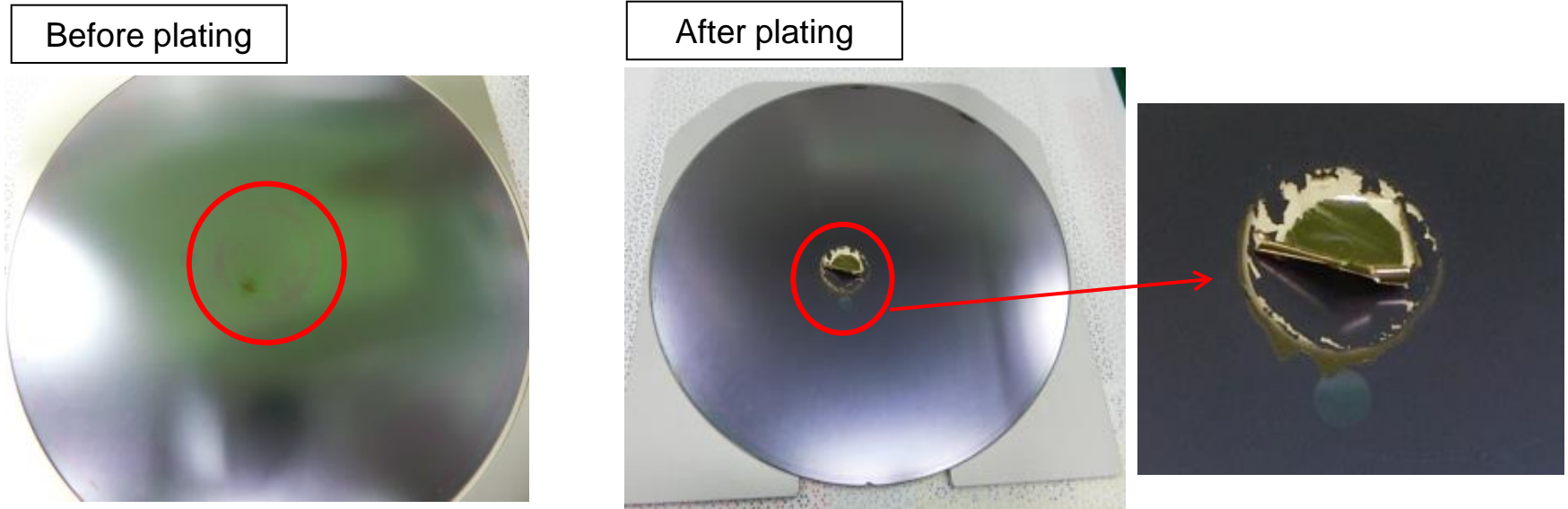


× 200

There were some tiny dimples at the back-side.  
After the plating process, abnormal Au plating was observed on the dimples.

# Example of unsuitable wafer for Electroless plating (2)

## Surface contaminations on wafer (Abnormal plating)

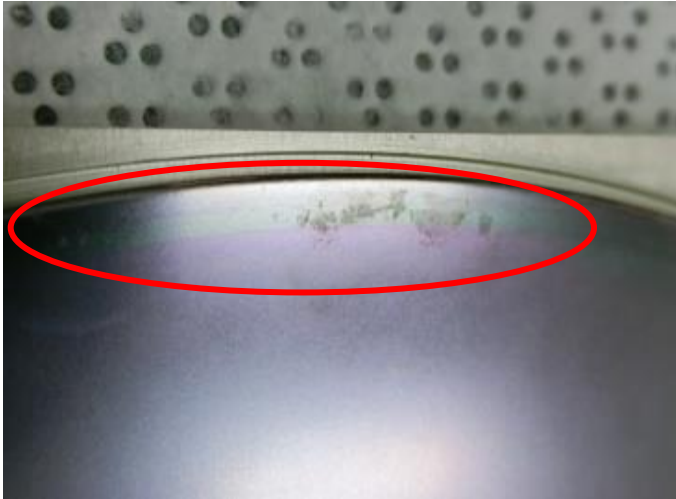


Abnormal Au plating and peeling of plating film were observed at backside.

# Example of unsuitable wafer for Electroless plating (3)

## Surface contaminations on wafer (Abnormal plating)

Before plating



After plating



Abnormal Au plating and peeling of plating film were observed at backside.

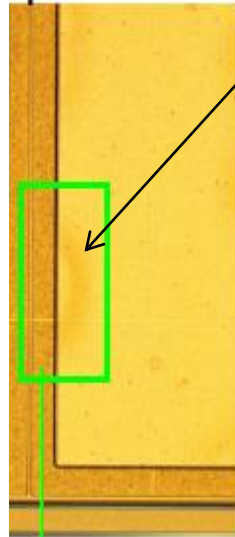
# Example of unsuitable wafer for Electroless plating (4)

## Insufficient adhesion of PI (Spot stain)

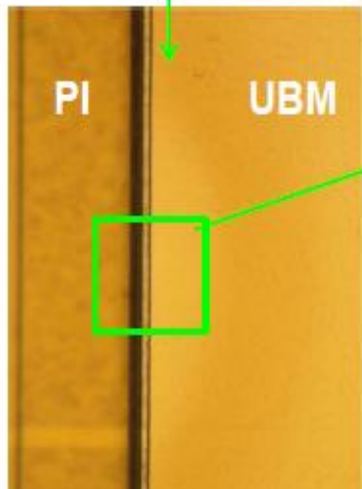
Optical microscope

Spot stain

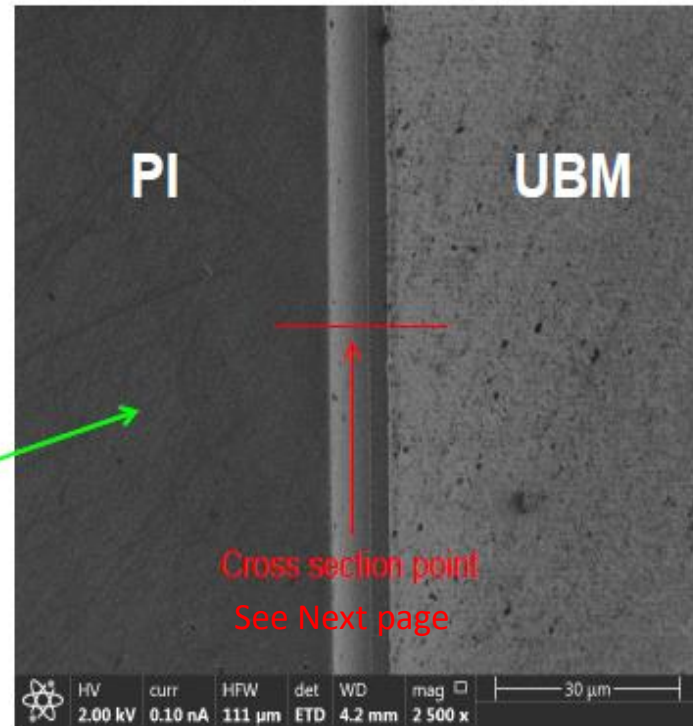
x100



x500



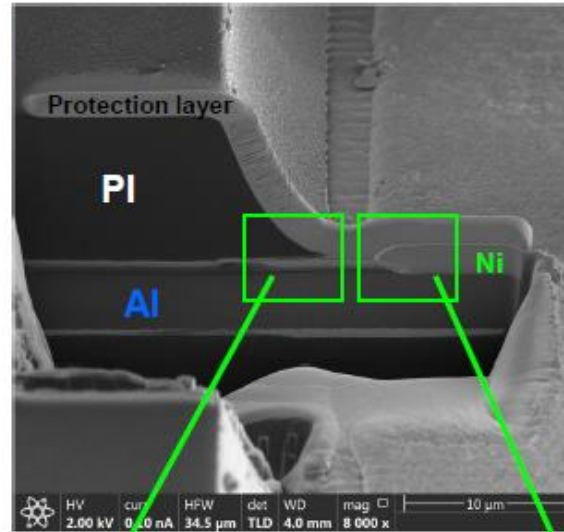
Top view(SIM Image)



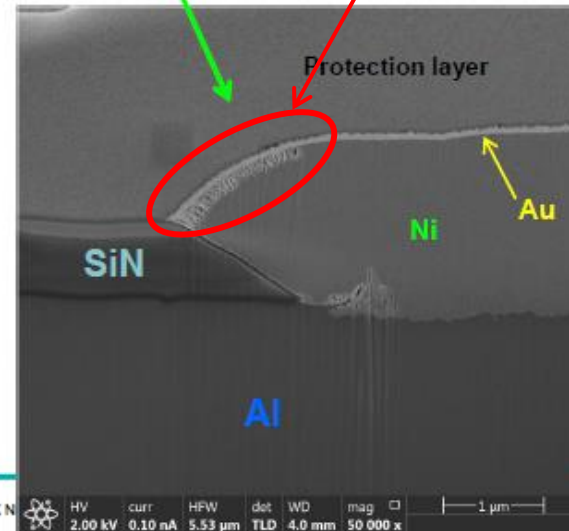
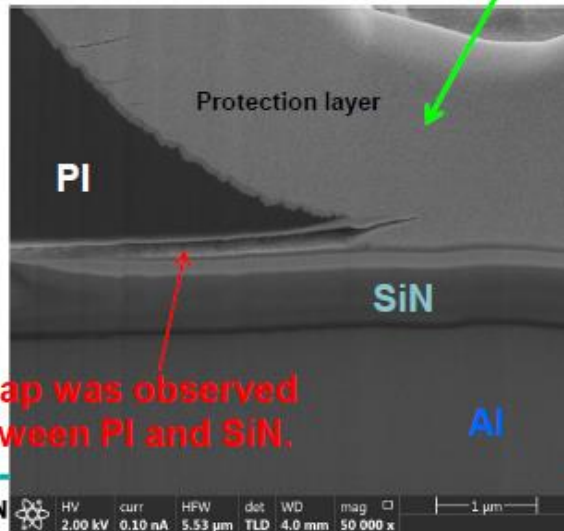
# Example of unsuitable wafer for Electroless plating (4)

## Insufficient adhesion of PI (Spot stain)

FIB/SIM image

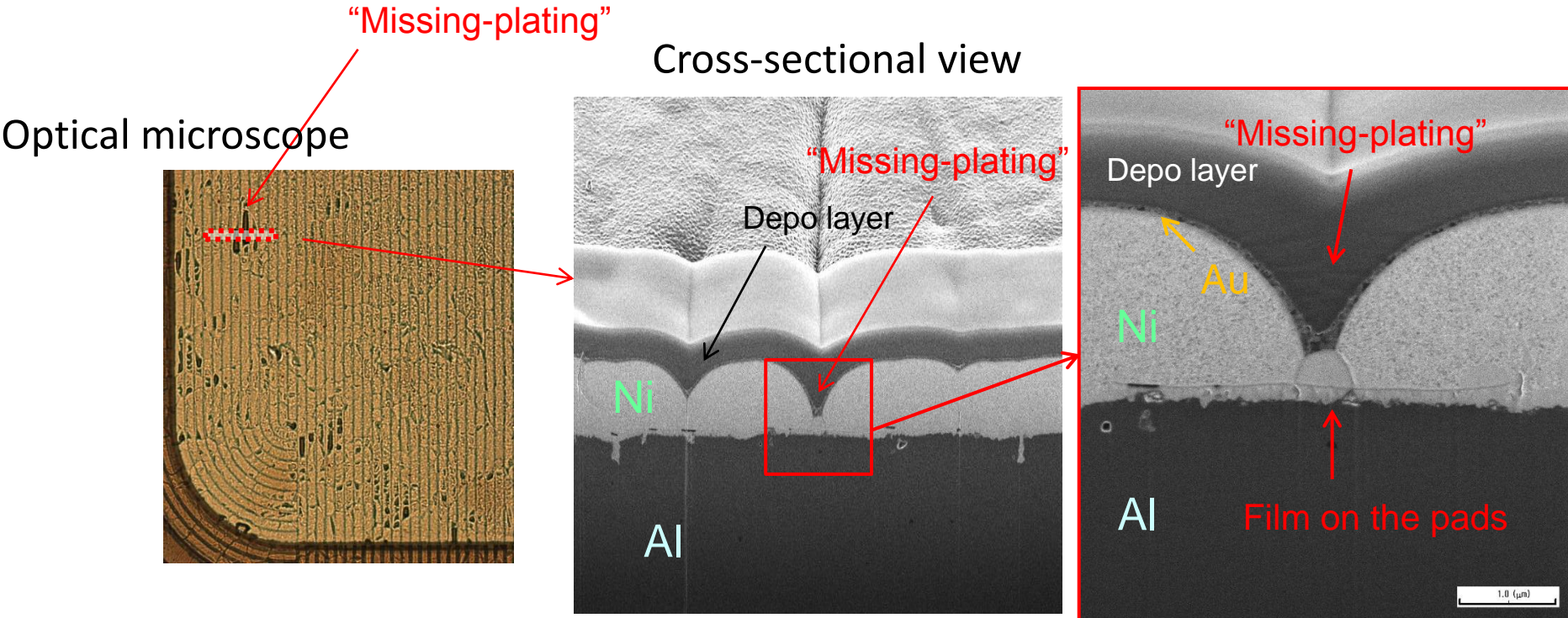


Spot stain



# Example of unsuitable wafer for Electroless plating (5)

## Surface contaminations on Pad (Missing plating)

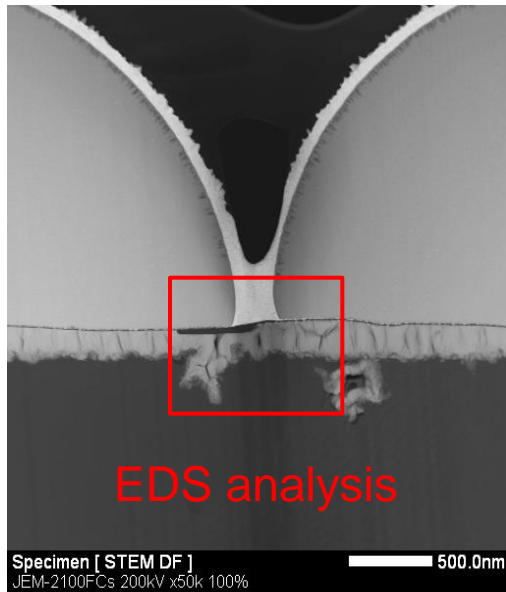


Something like film was observed on the Al-Cu pad at “missing-plating” point.

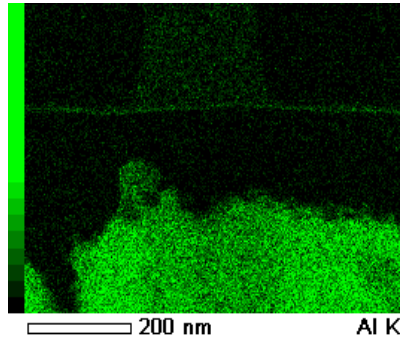
# Example of unsuitable wafer for Electroless plating (3)

## Surface contaminations on Pad (Missing plating)

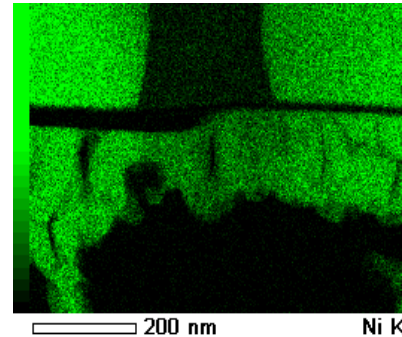
HAADF STEM image



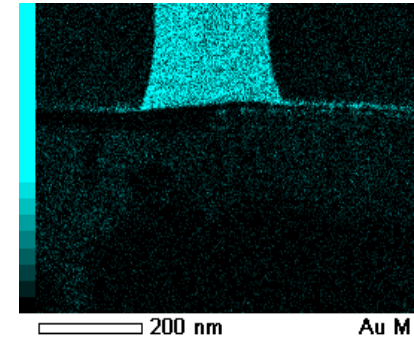
Al



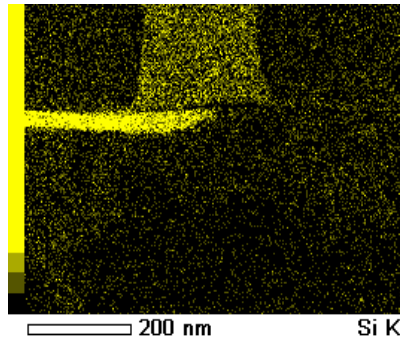
Ni



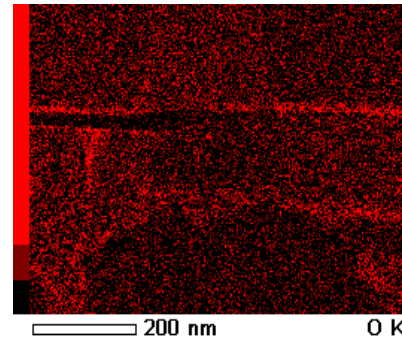
Au



Si



O



At “missing-plating” point, thin residue was observed on the Al-Cu pad.  
By EDS elemental analysis, Si was detected as component of the residue.